

## CORRECTION

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## Correction: Tunnel injection from WS<sub>2</sub> quantum dots to InGaN/GaN quantum wells

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Correction for 'Tunnel injection from WS<sub>2</sub> quantum dots to InGaN/GaN quantum wells' by Svette Reina Merden Santiago *et al.*, RSC Adv., 2018, **8**, 15399–15404.

Eqn (4) in the published paper was incorrect; the correct version is shown below:

$$\tau_T \propto \exp \left[ 2L \sqrt{(2m^*/\hbar^2)(V - E)} \right] \quad (4)$$

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.



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